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Mesoscopic transport properties of $LaAlO_3/SrTiO_3$ devices

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[1] A.Ohtomo et al., Nature 427, 423 (2004)
[2] A.D.Caviglia et al., Nature 456, 624 (2008); C.Bell et al., PRL 103, 226802 (2009)
[3] A.D.Caviglia et al., PRL 105, 236802 (2010)
[4] M.Ben Shalom et al., PRL 105,206401 (2010)

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